Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A substrate device, comprising:

thin film transistors provided above a substrate, each including a semiconductor layer; and

capacitors formed above the thin film transistors, each of the capacitors comprising a first electrode electrically connected to a part of the semiconductor layer, a second electrode arranged to face the first electrode, and a dielectric film including a nitride film arranged between the first electrode and the second ~~electrode;~~electrode such that the first electrode is at a bottom surface of the nitride film and the second electrode is at a top surface of the nitride film; the nitride film having an aperture formed vertically above the semiconductor layer in plan view.

2. (Canceled)

3. (Previously Presented) The substrate device according to Claim 1, the aperture being formed vertically above a channel region of the semiconductor layer.

4. (Original) The substrate device according to Claim 1, the dielectric film having a laminated structure including a layer formed of the nitride film.

5. (Original) The substrate device according to Claim 4, a layer formed of an oxide film being included in the laminated structure.

6. (Original) The substrate device according to Claim 1, the plurality of thin film transistors being arranged above the substrate in array.

7. (Currently Amended) An electro-optical device, comprising:

scanning lines extending above a substrate;

data lines extending in a direction intersecting the scanning lines;

thin film transistors formed to correspond to each intersection between the scanning lines and the data lines, each including a semiconductor layer;

pixel electrodes provided to correspond to the thin film transistors; and

storage capacitors formed above the thin film transistors, each of the storage capacitors comprising a first electrode electrically connected to a part of the semiconductor layer, a second electrode arranged to face the first electrode, and a dielectric film including a nitride film arranged between the first electrode and the second ~~electrode;~~electrode such that the first electrode is at a bottom surface of the nitride film and the second electrode is at a top surface of the nitride film; the nitride film having an aperture formed vertically above the semiconductor layer in plan view.

8. (Original) The electro-optical device according to Claim 7, the apertures being formed within regions where the pixel electrodes are formed.

9. (Original) The electro-optical device according to Claim 7, the pixel electrodes and the thin film transistors being arranged in a matrix and the scanning lines are formed in stripes to correspond to the matrix, the device further comprising capacitive lines of fixed potential formed parallel to the scanning lines, and the capacitive lines including the second electrodes.

10. (Original) The electro-optical device according to Claim 7, further comprising:

first contact holes that electrically connect the first electrodes to a part of the semiconductor layer; and

second contact holes that electrically connect the first electrodes to the pixel electrodes.

11. (Original) The electro-optical device according to Claim 7, the thin film transistors being a plurality of N-channel type thin film transistors arranged in array, and the

thin film transistors being provided in pixels in an image display region above the substrate for switching the pixels.

12. (Original) The electro-optical device according to Claim 7, the data lines overlapping the apertures.

13. (Original) The electro-optical device according to Claim 7, the nitride films being formed on the front surfaces of pixel regions, and the apertures being formed at the edge of the pixel electrodes.

14. (Canceled)

15. (Currently Amended) An electronic apparatus, comprising:

scanning lines extending above a substrate;

data lines extending in a direction intersecting the scanning lines;

thin film transistors formed to correspond to each of intersections between the scanning lines and the data lines, each including a semiconductor layer;

pixel electrodes provided to correspond to the thin film transistors; and

storage capacitors formed above the thin film transistors, each of the storage capacitors comprising a first electrode electrically connected to a part of the semiconductor layer, a second electrode arranged to face the first electrode, and a dielectric film including a nitride film arranged between the first electrode and the second ~~electrode;~~electrode such that the first electrode is at a bottom surface of the nitride film and the second electrode is at a top surface of the nitride film; the nitride film having an aperture formed vertically above the semiconductor layer in plan view.